



**PRELIMINARY**  
 Notice: This is not a final specification.  
 Some parametric limits are subject to change.

**ELECTRICAL CHARACTERISTICS** (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	Id = 1mA, VGS = 0V	250	—	—	V
IGSS	Gate-source leakage current	VGS = ±20V, VDS = 0V	—	—	±10	μA
IDSS	Drain-source leakage current	VDS = 250V, VGS = 0V	—	—	1	mA
VGS (th)	Gate-source threshold voltage	Id = 1mA, VDS = 10V	2.0	3.0	4.0	V
rDS (ON)	Drain-source on-state resistance	Id = 6A, VGS = 10V	—	0.27	0.40	Ω
VDS (ON)	Drain-source on-state voltage	Id = 6A, VGS = 10V	—	1.62	2.40	V
yfs	Forward transfer admittance	Id = 6A, VDS = 10V	—	11.0	—	S
Ciss	Input capacitance	VDS = 25V, VGS = 0V, f = 1MHz	—	1200	—	pF
Coss	Output capacitance		—	120	—	pF
Crss	Reverse transfer capacitance		—	30	—	pF
td (on)	Turn-on delay time		—	20	—	ns
tr	Rise time	VDD = 150V, Id = 6A, VGS = 10V, RGEN = RGS = 50Ω	—	30	—	ns
td (off)	Turn-off delay time		—	190	—	ns
tf	Fall time		—	45	—	ns
VSD	Source-drain voltage	IS = 6A, VGS = 0V	—	0.95	—	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	1.92	°C/W